SPTECH Silicon NPN Power Transistor

2SD717

DESCRIPTION

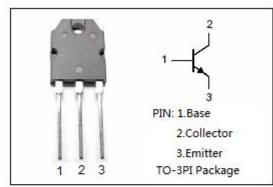
- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 50V (Min)
- · Low Collector-Emitter Saturation Voltage-
 - : V_{CE(sat)}= 0.4V (Max)@I_C= 6.0A
- · High Collector Power Dissipation
 - : P_C= 80W @T_C=25℃

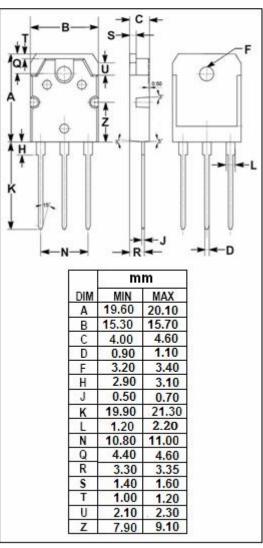


- High power switching applications
- DC-DC converter and DC-AC inverter applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|------------|------------|--|
| V_{CBO} | Collector-Base Voltage | 70 | V | |
| V _{CEO} | Collector-Emitter Voltage | 50 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| Ic | Collector Current-Continuous | 10 | А | |
| I _B | Base Current-Continuous | 2.5 | А | |
| Pc | Collector Power Dissipation @ T _C =25℃ | 80 | W | |
| TJ | Junction Temperature | 150 | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range | -55~150 °C | | |





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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _(BR) CEO | Collector-Emitter Breakdown Voltage | Ic= 1mA; I _B = 0 | 50 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 6A; I _B = 0.3A | | | 0.4 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 6A; I _B = 0.3A | | | 1.2 | V |
| І _{сво} | Collector Cutoff Current | V _{CB} = 70V ; I _E = 0 | | | 10 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V ; I _C = 0 | | | 10 | μА |
| h _{FE -1} | DC Current Gain | Ic= 1A; Vc== 1V | 70 | | 240 | |
| h _{FE -2} | DC Current Gain | I _C = 6A ; V _{CE} = 1V | 30 | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 1A; V _{CE} = 4V | | 10 | | MHz |
| Сов | Output Capacitance | I _E = 0 ; V _{CB} = 10V;f _{test} = 1.0MHz | | 350 | | pF |
| Switching times | | | | | | |
| | | | | | | |

| t _{on} | Turn-on Time | | 0.3 | μS |
|------------------|--------------|--|-----|----|
| t _{stg} | Storage Time | $ \text{I}_{\text{C}} = 6\text{A} , _{\text{B}1} = _{\text{B}2} = 0.3\text{A}; \text{R}_{\text{L}} = 5\Omega ; \text{V}_{\text{CC}} = 30\text{V}; \text{P}_{\text{W}} = 20\mu \text{ s;Duty Cycle} \le 1\%$ | 2.5 | μS |
| t _f | Fall Time | | 0.4 | μS |

♦ h_{FE-1} Classifications

| 0 | Y |
|--------|---------|
| 70-140 | 120-240 |

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